

10th Nanowire Growth Workshop + 9th Nanowires

NANOWIRE WEEK 2017

May 29th - June 2nd, Lund, Sweden





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Daniel Jacobsson, Luna Namazi, Reza R. Zamani, Sebastian Lehmann, Magnus Heurlin, Malin Nilsson, Henrik Persson, and Gustav Nylund are gratefully acknowledged for images and figures presented on the cover. Reza R. Zamani is gratefully acknowledged for the cover art.



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Welcome Message

I would like to welcome you to Lund, and to Nanowire Week! We are very excited and proud to be hosting the first major international meeting covering all aspects of nanowire research, from growth to applications.

Nanowire Week has been created by merging two of the most important and well-established workshops in our field, NANOWIRES and the Nanowire Growth Workshop. The core purpose of this meeting is therefore to bring together researchers from different parts of the nanowire community for a week of lively discussion and debate on the latest topics in nanowire research.

The very first Nanowire Growth Workshop was held right here in Lund, a bit more than a decade ago in late 2006. The purpose of the meeting was to gather a group of colleagues for open discussions about some of the central questions in our field. This year would have been the 10th NGW, making it a very fitting time to evolve into a new form. NANOWIRES workshop started in 2008, with a somewhat broader focus on different areas of nanowire research, but a similar central purpose of open discussion on topics of general interest. In the last few years the scope of these two workshops have become complementary and they have been held together, consecutively, for the past two occasions.

Nanowire Week: builds on the strengths of NANOWIRES and the Nanowire Growth Workshop, bringing together nanowire researchers across traditional disciplinary boundaries. We are pleased to welcome 330 participants to Nanowire Week, representing 25 countries. The technical program is made up of 14 invited and plenary presentations, 49 contributed oral presentations, and 177 poster presentations, in addition to social activities and panel discussions on hot topics in nanowire research.

I would like to warmly thank the Local Organizing Committee, Program Committee and the International Steering Committee for all of their hard work in making this meeting possible. I would also like to thank our sponsors for their interest and support of our workshop.

Finally, I'd like to thank you all for joining us here in Lund, and look forward to spending the week with you!

Kimberly Thelander
Nanowire Week Chair

Innovation of the Ultimate LV-STEM

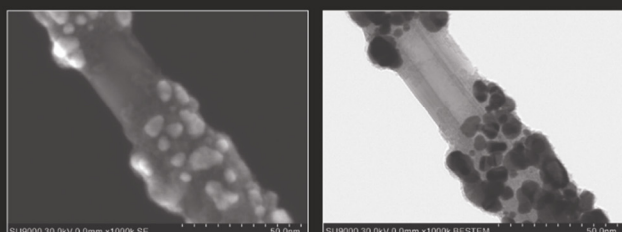
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SEM/STEM/STEM Simultaneous Imaging

Surface & Volume information simultaneously



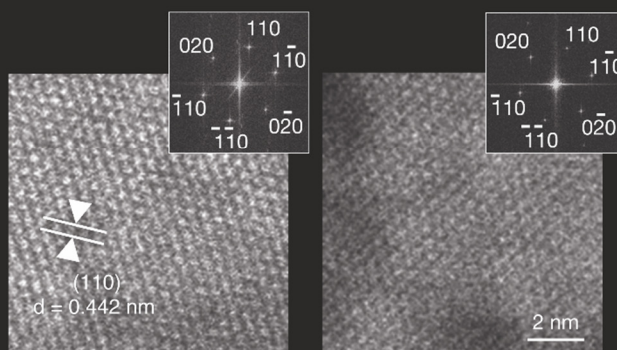
SE image

BF-STEM image

Specimen :
CNT coated by Polybenzimidazole attached with Platinum Nanoparticle

Specimen Courtesy :
A. Prof. Tsuyohiko Fujigaya, Department of Applied Chemistry,
Faculty of Engineering, Kyushu University

Low-Voltage Low-Voltage Lattice Imaging

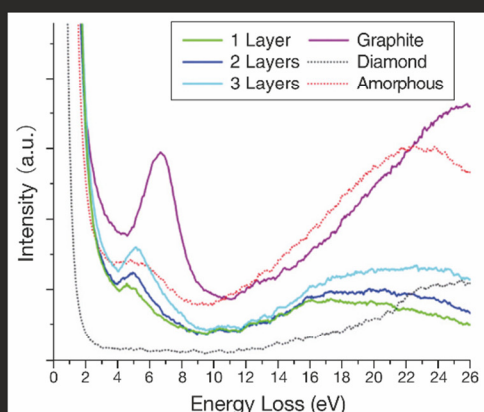


Vacc : 30 kV

Vacc : 7 kV

Specimen : Pyrophyllite

30 kV STEM/EELS



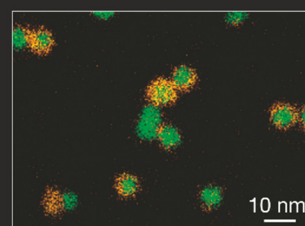
EEL spectra of graphene, amorphous carbon, graphite and diamond

Chemical analysis using STEM/EELS technique is now demonstrated at 30 kV (C, N, O, etc.).

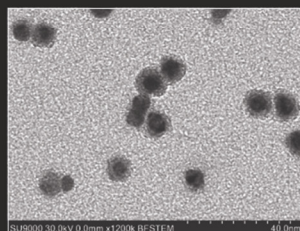
30 kV STEM/EDS

Specimen :
Silver-Copper Nanoparticle

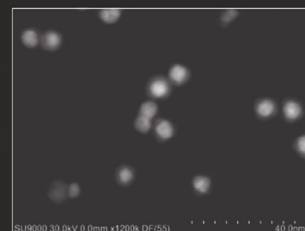
Specimen courtesy :
Dr. Dai Mochizuki,
Department of Applied Chemistry,
Tokyo Institute of Technology



Ag/Cu EDS Layer map
(Orange : Cu-K, Green : Ag-L)



BF-STEM image



DF-STEM image

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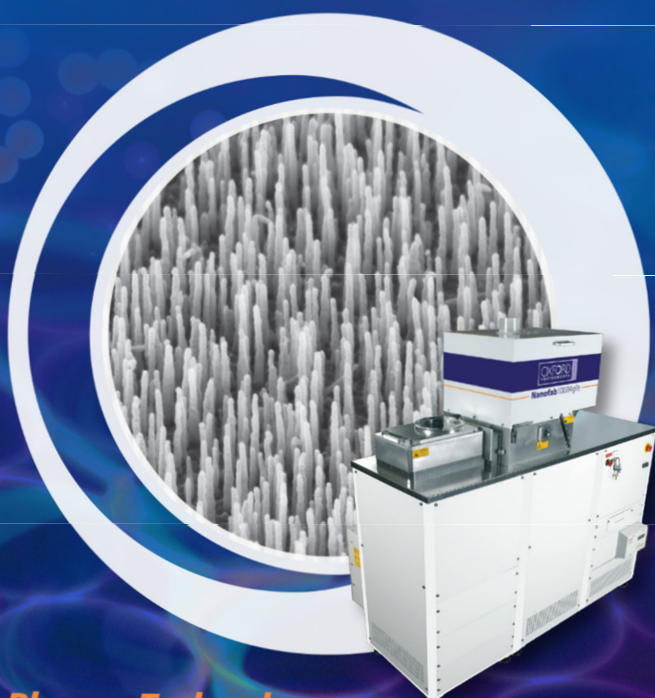
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Leading Edge Nanotechnology Tools



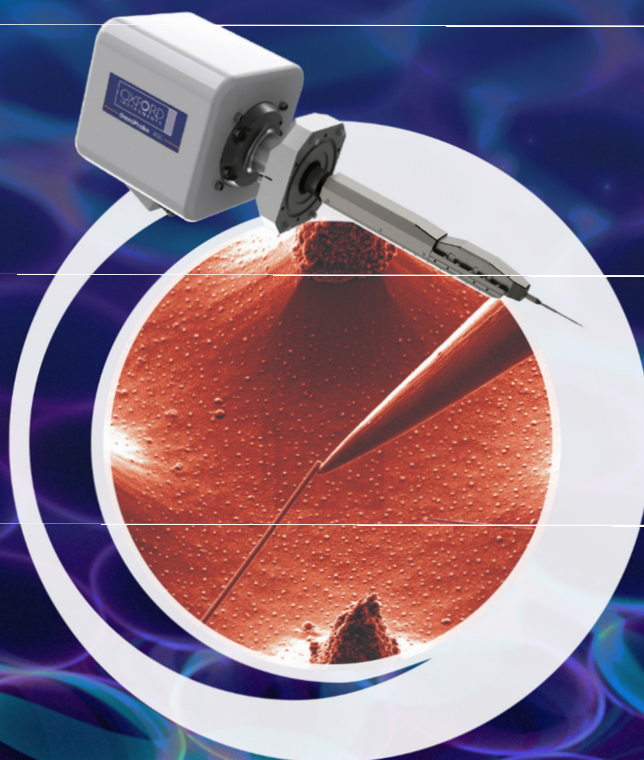
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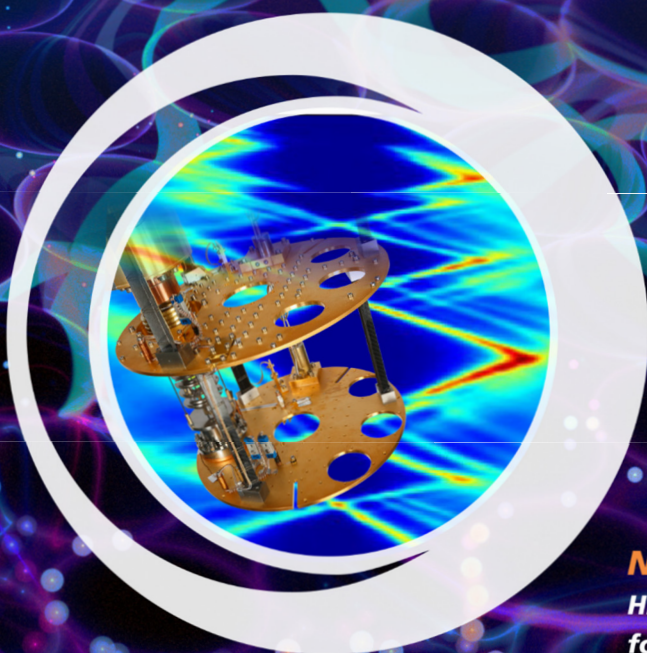
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growth of nanowires*



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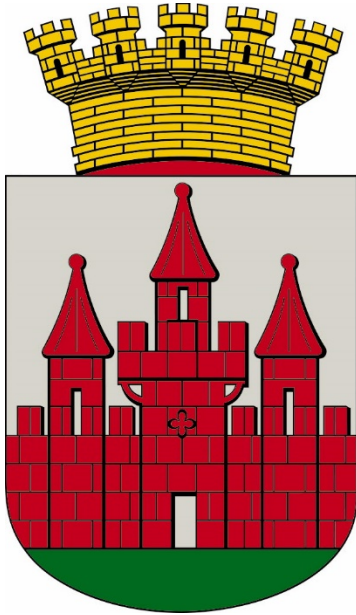
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NANOWIRE WEEK 2017,
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	Monday, May 29	Tuesday, May 30	Wednesday, May 31	Thursday, June 1	Friday, June 2
09:00	09:00 – 09:20 Opening Remarks	09:00 – 09:30 <i>Invited:</i> M. Takahashi	09:00 – 09:30 <i>Invited:</i> K. Kavanagh	09:00 – 09:30 <i>Invited:</i> J. Petta	09:00 – 09:30 <i>Invited:</i> J. Gooth
09:30	09:20 – 10:00 Plenary Session F. Glas	09:30 – 09:50 L. Feigl	09:30 – 09:50 E. Fiordaliso	09:30 – 09:50 L. Francaviglia	09:30 – 09:50 F. Lindelöw
10:00	10:00 – 10:20 M. Ghasemi	09:50 – 10:10 M. Hill	09:50 – 10:10 V. Piazza	09:50 – 10:10 S. Gasibegović	09:50 – 10:10 S. Sergent
10:30	10:20 – 10:40 H. Potts	10:10 – 10:30 D. Pan	10:10 – 10:30 D. Tedeschi	10:10 – 10:30 F. Viñas	10:10 – 10:30 J. Boland
11:00	10:40 – 11:20 Coffee	10:30 – 11:10 Coffee	10:30 – 11:10 Coffee	10:30 – 11:10 Coffee	10:30 – 11:10 Coffee
11:30	11:20 – 11:50 <i>Invited:</i> U. Pietsch	11:10 – 11:40 <i>Invited:</i> P. Caroff	11:10 – 11:40 <i>Invited:</i> A. Cros	11:10 – 11:40 <i>Invited:</i> M. De Luca	11:10 – 11:40 <i>Invited:</i> R. Songmuang
12:00	11:50 – 12:10 Y. Ren	11:40 – 12:00 K. Tomioka	11:40 – 12:00 O. Persson	11:40 – 12:00 R. Tanta	11:40 – 12:00 M. Spies
12:30	12:10 – 12:30 M. Sobanska	12:00 – 12:20 J.-H. Kang	12:00 – 12:20 P. Alekseev	12:00 – 12:20 B. Spann	12:00 – 12:20 J.A. Alanis Azuara
	12:30 – 13:00 <i>Invited:</i> L. Lauhon	12:20 – 12:40 T. Kanne	12:20 – 12:40 Y. Calahorra	12:20 – 12:40 I.-J. Chen	12:20 – 12:40 K. Zimmermann
13:00	13:00 – 14:00 Lunch	12:40 – 13:00 R.B. Lewis	12:40 – 12:45 Technical Session	12:40 – 13:00 S. Roddaro	12:40 – 14:00 Lunch
13:30		13:00 – 14:00 Lunch	12:45 – 14:00 Lunch	13:00 – 14:00 Lunch	
14:00	14:00 – 16:00 Poster Session 1	14:00 – 16:00 Poster Session 2	14:00 – 15:30 Social Program	14:00 – 16:00 Poster Session 3	14:00 – 14:30 <i>Invited:</i> Z. Mi
14:30					14:30 – 14:50 S. Hoelzel
15:00					14:50 – 15:10 D. Carrod
15:30			15:30 – 16:00 Coffee		15:10 – 15:30 K. Adolfsson
16:00	16:00 – 16:20 J. Červenka	16:00 – 16:20 A. Ajay	16:00 – 17:30 Social Program	16:00 – 16:20 J. Muessener	15:30 – 16:00 Closing Remarks
16:30	16:20 – 16:40 M. Zavarize	16:20 – 16:40 S. Lancaster		16:20 – 16:40 D. Salomon	
	16:40 – 17:00 J. Becdelievre	16:40 – 17:00 K. Kawaguchi		16:40 – 17:00 J. Wallentin	
17:00	17:00 – 17:30 Coffee	17:00 – 17:30 Coffee		17:00 – 17:30 Coffee	
17:30	17:30 – 18:00 <i>Invited:</i> V. Zannier	17:30 – 17:50 K. Mølhav		17:30 – 18:00 <i>Invited:</i> H. Krenner	
18:00	18:00 – 18:20 A. Scaccabarozzi	17:50 – 18:10 A. van Helvoort		18:00 – 18:20 F. Rossella	
	18:20 – 18:40 J.-C. Harmand	18:10 – 18:30 Z.-X. Yang		18:20 – 18:40 J. Becker	
18:40					
19:00			19:00 – 23:00 Dinner		

Panel Discussions

Wednesday May 31st

Session 1 - 14:00

1. “Nanowires will never compete with established Si-based technology in for example CMOS and photovoltaics” – agree or disagree?

What remains to be solved for nanowires to make a real impact? For what applications do you envision nanowires will first appear in product form?

Chair: Anna Fontcuberta i Morral (EPFL Lausanne, Switzerland)

*Panel: Mikael Björk (QuNano AB Lund, Sweden)
Werner Prost (University Duisburg-Essen, Germany)
Heike Riel (IBM Zurich, Switzerland)*

2. Do nanowire properties differ in any meaningful way from bulk materials?

Low-dimensional materials are predicted to have unique physical properties; however most nanowires studied today are essentially just small rods of bulk material. To what extent do we need to downscale the dimensions in order to observe the predicted low-dimensional effects? Is it worth the effort - are the proposed effects relevant/interesting for any particular application, or just a curiosity?

Chair: Lutz Geelhaar (PDI Berlin, Germany)

*Panel: Hubert J. Krenner (University Augsburg, Germany)
Faustino Martelli (CNR-IMM Rome, Italy)
Val Zwiller (KTH Stockholm, Sweden)*

Session 2 - 16:00

3. Is gold-seeded VLS still the best way to form nanowires?

Most early studies of semiconductor nanowires used bottom-up structures grown using Au catalysts. Have other methods such as self-catalyzed or selective area growth reach a point where they are superior? Are there advantages to VSS as an alternative? Is there any real advantage to any of these methods or is more conventional top-down etching the way to go for most applications?

Chair: Michael A. Filler (Georgia Tech., USA)

*Panel: Mattias Borg (Lund University, Sweden)
Philippe Caroff (Cardiff University, UK)
Vladimir G. Dubrovskii (St. Petersburg University, Russia)*

4. Nanowires for condensed matter physics – are they as good as we think?

Nanowires are widely considered ideal structures for investigating exotic phenomena in condensed matter (following for example their use in Majorana fermion investigations). Are these materials really suitable, in terms of geometry, purity, properties...? What qualities are needed to make nanowires useful in this way? Is it really viable to form/grow structures with the desired properties?

Chair: Erik P.A.M. Bakkers (University Eindhoven, The Netherlands)

*Panel: Sergey Frolov (University of Pittsburgh, USA)
Jason Petta (Princeton University, USA)
Stefano Roddaro (IN-CNR and University Pisa, Italy)*



ORAL SESSIONS



NANOWIRE WEEK 2017,
May 29th — June 2nd, Lund, Sweden

Oral Sessions

Monday, May 29, 2017

8:00 – 9:00 Registration

9:00 – 9:20 Opening remarks

9:20 – 10:40	Oral Session M1	Chair: Kimberly Thelander
9:20 – 10:00	Frank Glas C2N, CNRS, Université Paris-Sud, France <i>Polytypism in semiconductor nanowires</i>	Plenary
10:00 – 10:20	Masoomah Ghasemi Solid State Physics/NanoLund, Lund University, Sweden Division of Computational Thermodynamics, KTH Royal Inst. Tech., Sweden <i>Thermodynamic modeling of Sn-seeded InAs, GaAs and In_xGa_{1-x}As nanowires</i>	Contributed M1.1
10:20 – 10:40	Heidi Potts Laboratoire des Matériaux Semiconducteurs, EPFL, Switzerland <i>Self-catalyzed InAs nanowires in many different directions by MBE</i>	Contributed M1.2
10:40 – 11:20	Coffee Break	
11:20 – 13:00	Oral Session M2	Chair: Paul McIntyre
11:20 – 11:50	Ullrich Pietsch Faculty of Science and Engineering, University of Siegen, Germany <i>Ex-situ and in-situ X-ray nano-diffraction analysis of the structure of core-shell-shell semiconductor nanowires</i>	Invited I1
11:50 – 12:10	Yizhen Ren Department of Applied Physics, Eindhoven Uni. Tech., Netherlands <i>Making silicon complete -- Direct bandgap hexagonal Si_{1-x}Ge_x alloy</i>	Contributed M2.1
12:10 – 12:30	Marta Sobanska Institute of Physics, Polish Academy of Sciences, Poland <i>Comprehensive analysis of self-assembled formation of GaN nanowires on Al_xO_y: in situ quadrupole mass spectrometry studies</i>	Contributed M2.2
12:30 – 13:00	Lincoln J. Lauhon Department of Materials Science & Engineering, Northwestern University, U.S.A. <i>Kinking induced dopant modulation in VLS grown Si nanowires</i>	Invited I2

13:00 – 14:00 Lunch

14:00 – 16:00 Poster Session P1 (with coffee served at 15:30)

16:00 – 17:00	Oral Session M3	Chair: Michael Filler
16:00 – 16:20	Jiří Červenka Dep. Thin Films and Nanostructures, Inst. Physics ASCR, Czech Republic <i>Low-temperature growth of in-plane and out-of-plane silicon nanowires</i>	Contributed M3.1
16:20 – 16:40	Mariana Zavarize Applied Physics Dep., Inst. Physics "Gleb Wataghin", State Uni. Campinas, Brazil <i>Ag-catalyzed wurtzite InP nanowires</i>	Contributed M3.2
16:40 – 17:00	Jeanne Becdelievre University of Lyon, Institut des Nanotechnologies de Lyon (INL), France <i>Ultra-long self-catalyzed GaAs nanowires grown by Molecular Beam Epitaxy on Si(111)</i>	Contributed M3.3

17:00 – 17:30 Refreshment Break

17:30 – 18:40	Oral Session M4	Chair: Philippe Caroff
17:30 – 18:00	Valentina Zannier NEST, Istituto Nanoscienze – CNR and Scuola Normale Superiore, Italy <i>Catalyst composition tuning: the key for the growth of straight axial nanowire heterostructures</i>	Invited I3
18:00 – 18:20	Andrea Scaccabarozzi Institut Photovoltaïque d'Île-de-France (IPVF), CNRS, France <i>Stabilizing effect of Indium in the vertical growth of self-catalyzed GaAs and GaP nanowire arrays by MBE</i>	Contributed M4.1
18:20 – 18:40	Jean-Christophe Harmand C2N, CNRS, Université Paris-Sud, France <i>In situ growth of GaAs nanowires by molecular beam epitaxy in a high-resolution transmission electron microscope</i>	Contributed M4.2

Tuesday, May 30, 2017

9:00 – 10:30	Oral Session Tu1	Chair: Rainer Timm
9:00 – 9:30	Masamitsu Takahasi National Institutes for Quantum and Radiological Science & Technology, Japan <i>Atomic ordering and nucleation at the AuGa droplet-GaAs crystal interface studied by in situ X-ray diffraction</i>	Invited I4
9:30 – 9:50	Ludwig Feigl Inst. for Photon Science & Synchrotron Radiation, Karlsruhe Inst.Tech., Germany <i>Time-resolved in-situ X-ray investigations during growth of In_xGa_{1-x}As core-shell nanowire structures</i>	Contributed Tu1.1
9:50 – 10:10	Megan O. Hill Department of Materials Science & Engineering, Northwestern University, U.S.A. <i>Analysis of stacking disorder in InGaAs nanowires using 2D Bragg Projection Ptychography</i>	Contributed Tu1.2
10:10 – 10:30	Dong Pan Institute of Semiconductors, Chinese Academy of Sciences, China <i>Near full-composition-range high-quality GaAs_{1-x}Sb_x nanowires grown by molecular-beam epitaxy</i>	Contributed Tu1.3
10:30 – 11:10	Coffee Break	
11:10 – 13:00	Oral Session Tu2	Chair: Anna Fontcuberta I Morral
11:10 – 11:40	Philippe Caroff School of Physics and Astronomy, Cardiff University, U.K. <i>Shape engineering in III-V nanostructures beyond the nanowire geometry</i>	Invited I5
11:40 – 12:00	Katsuhiko Tomioka Research Center for Integrated Quantum Electronics, Hokkaido University, Japan <i>Selective-area growth of InGaAs nanowires with various In compositions on Ge(111) substrates</i>	Contributed Tu2.1
12:00 – 12:20	Jung-Hyun (Jordan) Kang Braun Center for Submicron Research, Weizmann Institute of Science, Israel <i>Wurtzite/zinc-blende interconnected InAs nanowires with embedded two-dimensional wurtzite plates</i>	Contributed Tu2.2
12:20 – 12:40	Thomas Kanne Niels Bohr Institute, University of Copenhagen, Denmark <i>Epitaxial InAsSb/Al hybrid nanowire materials for topological superconductivity</i>	Contributed Tu2.3
12:40 – 13:00	Ryan B. Lewis Paul-Drude-Institut für Festkörperelektronik, Germany <i>Bismuth surfactant-induced self-assembly of InAs nanostructures on the {110} sidewalls of GaAs nanowires</i>	Contributed Tu2.4
13:00 – 14:00	Lunch	
14:00 – 16:00	Poster Session 2 (with coffee served at 15:30)	
16:00 – 17:00	Oral Session Tu3	Chair: Karen Kavanagh
16:00 – 16:20	Akhil Ajay University Grenoble-Alpes, CEA-INAC-PHELIQS & CNRS-Institut Néel, France <i>Germanium vs. silicon doping of GaN/AlN nanowire heterostructures for intersubband optoelectronics at 1.55 μm</i>	Contributed Tu3.1
16:20 – 16:40	Suzanne Lancaster Institute for Solid State Electronics, TU Wien, Austria <i>Incorporation of Boron in GaAs nanowires grown by self-catalysed molecular beam epitaxy</i>	Contributed Tu3.2
16:40 – 17:00	Kenichi Kawaguchi Fujitsu Limited, Wireless System Div., Atsugi, Japan <i>Heavily sulfur-doped InAs nanowires formed by position-controlled VLS growth method</i>	Contributed Tu3.3

17:00 – 17:30 Refreshment Break

17:30 – 18:40	Oral Session Tu4	Chair: Reza Zamani
17:30 – 17:50	Kristian Mølhave Department of Micro- and Nanotechnology, Technical University of Denmark, Denmark <i>In situ TEM current-voltage characteristics of in situ grown VLS silicon nanowire devices</i>	Contributed Tu4.1
17:50 – 18:10	Antonius T. J. van Helvoort Department of Physics, Norwegian Uni. Science & Tech. (NTNU), Norway <i>Improved compositional mapping of heterostructured nanowires</i>	Contributed Tu4.2
18:10 – 18:30	Zai-Xing Yang School of Microelectronics and Center of Nanoelectronics, Shandong Uni., China <i>Controllable growth of high-performance GaSb thin nanowires by a surfactant assisted CVD process</i>	Contributed Tu4.3

Wednesday, May 31, 2017

9:00 – 10:30	Oral Session W1	Chair: Werner Prost
9:00 – 9:30	Karen Kavanagh Department of Physics, Simon Fraser University, Canada <i>Imaging GaAs nanowire zinc dopant incorporation</i>	Invited I6
9:30 – 9:50	Elisabetta M. Fiordaliso Center for Electron Nanoscopy, Technical University of Denmark, Denmark <i>Characterization of doping distribution in GaAs nanowires by off-axis electron holography</i>	Contributed W1.1
9:50 – 10:10	Valerio Piazza C2N, CNRS, Université Paris-Sud, France <i>Electron beam induced current and cathodoluminescence study of InGaP/InP single nanowires containing two p-i-n junctions</i>	Contributed W1.2
10:10 – 10:30	Davide Tedeschi Dipartimento di Fisica, Sapienza Università di Roma, Italy <i>Spin and transport properties of electrons and holes in InP wurtzite nanowires assessed by magneto-optical measurements and k-p calculations</i>	Contributed W1.3

10:30 – 11:10 Coffee Break

11:10 – 12:40	Oral Session W2	Chair: Marta De Luca
11:10 – 11:40	Ana Cros Stotter Institute of Materials Science (ICMUV), University of Valencia, Spain <i>Electric force microscopy for the characterization of nitride semiconductor nanowires</i>	Invited I7
11:40 – 12:00	Olof Persson Synchrotron Radiation Research and NanoLund, Lund University, Sweden <i>Conductance and surface characterization of wurtzite/zinc blende InAs nanowires using scanning tunneling microscopy and spectroscopy</i>	Contributed W2.1
12:00 – 12:20	Prokhor A. Alekseev Ioffe Institute, Russia <i>Unified mechanism of the Fermi level pinning on III-As nanowires surface</i>	Contributed W2.2
12:20 – 12:40	Yonatan Calahorra Department of Materials Science and Metallurgy, University of Cambridge, UK <i>Electromechanical properties of III-V nanowires: an uncharted territory</i>	Contributed W2.3
12:40 – 12:45	Technical Session	

12:45 – 14:00 Lunch + break (buses for optional tours depart at 13:50)

14:00 – 17:30 Free afternoon / social program

14:00 – 15:30 Social program session 1

15:30 – 16:00 Coffee served

16:00 – 17:30 Social program session 2

19:00 Workshop Dinner

Thursday, June 1, 2017

9:00 – 10:30	Oral Session Th1	Chair: Adam Burke
9:00 – 9:30	Jason M. Petta Department of Physics, Princeton University, U.S.A. <i>Quantum optics with electrically driven semiconductor nanowire quantum dots</i>	Invited I8
9:30 – 9:50	Luca Francaviglia Laboratoire des Matériaux Semiconducteurs, EPFL, Switzerland <i>Red-shifting of self-assembled single-photon emitters in core-shell nanowires</i>	Contributed Th1.1
9:50 – 10:10	Saša Gazibegović Delft Uni. Tech. & Eindhoven Uni. Tech., Netherlands <i>Bottom-up grown nanowire quantum devices</i>	Contributed Th1.2
10:10 – 10:30	Florinda Viñas Solid State Physics and NanoLund, Lund University, Sweden <i>Extracting band structure characteristics of GaSb/InAs core-shell nanowires from thermoelectric properties</i>	Contributed Th1.3
10:30 – 11:10	Coffee Break	
11:10 – 13:00	Oral Session Th2	Chair: Hubert Krenner
11:10 – 11:40	Marta De Luca Department of Physics, University of Basel, Switzerland <i>Phonon engineering in superlattices in III-V nanowires</i>	Invited I9
11:40 – 12:00	Rawa Tanta Niels Bohr Institute, University of Copenhagen, Denmark <i>Micro-Raman spectroscopy for detection of crystal stacking faults in III-V compounds and Sb molar fraction in InAs_{1-x}Sb_x nanowires</i>	Contributed Th2.1
12:00 – 12:20	Bryan T. Spann National Institute of Standards and Technology, Applied Physics Division, U.S.A. <i>GaN nanopillars grown on Si membranes as a nanophononic metamaterial for thermoelectric applications</i>	Contributed Th2.2
12:20 – 12:40	I-Ju Chen Solid State Physics and NanoLund, Lund University, Sweden <i>Thermoelectric power factor in quasi-one-dimensional nanowires</i>	Contributed Th2.3
12:40 – 13:00	Stefano Roddaro NEST, Scuola Normale Superiore and Istituto Nanoscienze-CNR, Italy <i>InAs nanowire superconducting tunnel junctions: Quasi-particle spectroscopy, thermometry and nanorefrigeration</i>	Contributed Th2.4
13:00 – 14:00	Lunch	
14:00 – 16:00	Poster Session 3 (with coffee served at 15:30)	
16:00 – 17:00	Oral Session Th3	Chair: Faustino Martelli
16:00 – 16:20	Jan Müßener Institut für Festkörperphysik, Universität Bremen, Germany <i>Bias-controlled optical transitions in GaN/AlN nanowire heterostructures</i>	Contributed Th3.1
16:20 – 16:40	Damien Salomon ESRF-The European Synchrotron, France <i>Probing optical properties of nanowires with a multimodal hard X-ray nanoprobe</i>	Contributed Th3.2
16:40 – 17:00	Jesper Wallentin Synchrotron radiation research, Lund University, Sweden <i>In operando characterization of single nanowire devices using nanofocused X-rays</i>	Contributed Th3.3
17:00 – 17:30	Refreshment Break	



17:30 – 18:40	Oral Session Th4	Chair: Jason Petta
17:30 – 18:00	Hubert J. Krenner Augsburg Centre for Innovative Technologies (ACIT), Uni. Augsburg, Germany <i>Acousto-optoelectronic spectroscopy – probing carrier transport in single nanowires in real time</i>	Invited I10
18:00 – 18:20	Francesco Rossella NEST, Scuola Normale Superiore and Istituto Nanoscienze-CNR, Italy <i>Tunable Esaki effect in broken-gap core-shell nanowires</i>	Contributed Th4.1
18:20 – 18:40	Jonathan Becker Walter Schottky Institute & Technical University Munich, Germany <i>Low dimensional transport phenomena in modulation-doped GaAs-based core-multishell nanowire field-effect transistors</i>	Contributed Th4.2

Friday, June 2, 2017

9:00 – 10:30	Oral Session F1	Chair: Ray Lapierre
9:00 – 9:30	Johannes Gooth IBM Research Zurich, Switzerland <i>From III-V integration towards ballistic nanowire quantum networks</i>	Invited I11
9:30 – 9:50	Fredrik Lindelöw Department of Electrical and Information Technology, Lund University, Sweden <i>High-performance field-effect transistors using selectively grown lateral InGaAs nanowires</i>	Contributed F1.1
9:50 – 10:10	Sylvain Sergent NTT Nanophotonic Center, Japan <i>Manipulating and tuning ultraviolet nanowire-induced photonic crystal nanocavities</i>	Contributed F1.2
10:10 – 10:30	Jessica L. Boland Department of Physics, University of Oxford, U.K. <i>Phase-Sensitive Single InP Nanowire Photoconductive Receivers for Broadband Terahertz Detection</i>	Contributed F1.3
10:30 – 11:10	Coffee Break	
11:10 – 12:40	Oral Session F2	Chair: Ana Cros Stotter
11:10 – 11:40	Rudeesun Songmuang Institut Néel, CNRS, France <i>Catalyst-free III-N nanowires: From MBE growth to single nanowire nanodevices</i>	Invited I12
11:40 – 12:00	Maria Spies Université Grenoble-Alpes, France <i>GaN/AlN nanowire photodetectors with bias-controlled spectral response</i>	Contributed F2.1
12:00 – 12:20	Juan Arturo Alanis Azuara School of Physics and Astronomy, University of Manchester, U.K. <i>(Al)GaAs multi-quantum-well nanolasers: correlations for optimization</i>	Contributed F2.2
12:20 – 12:40	Kseniia Zimmermann Inst. Semiconductor Tech., Braunschweig University of Technology, Germany <i>Spectral tailoring of the photoconductivity of semiconductor nanowires with carbon nanodots</i>	Contributed F2.3
12:40 – 14:00	Lunch + Break	
14:00 – 15:30	Oral Session F3	Chair: Lutz Geelhaar
14:00 – 14:30	Zetian Mi McGill University / University of Michigan, Canada/U.S.A. <i>Tuning the electronic structure of III-nitride nanowires for efficient light emitters and solar fuels generation</i>	Invited I13
14:30 – 14:50	Sara Hölzel I. Physikalisches Institut, Justus-Liebig-Universität, Gießen, Germany <i>InGaN/GaN nanowire heterostructures as multifunctional optical biosensors</i>	Contributed F3.1
14:50 – 15:10	Damon J. Carrad School of Physics, University of New South Wales, Australia <i>Hybrid nanowire ion-to-electron transducers for integrated bioelectronics circuitry</i>	Contributed F3.2
15:10 – 15:30	Karl Adolfsson Solid State Physics, Lund University, Sweden <i>Fluorescent heterostructure nanowires for biological applications</i>	Contributed F3.3
15:30 – 16:00	Closing Remarks	
16:00 – 16:30	Coffee and refreshments served	



POSTER SESSIONS



NANOWIRE WEEK 2017,
May 29th — June 2nd, Lund, Sweden

Poster Sessions

Monday, May 29, 2017

14:00 – 16:00 Poster Session P1

P1.1	Mihail Ion Lepsa Peter Grünberg Institute (PGI-9), Forschungszentrum Jülich, Germany <i>MBE growth of InAs/Al and InAs/Nb superconducting hybrid nanowire structures</i>
P1.2	Filip Krížek Niels Bohr Institute, University of Copenhagen, Denmark <i>Growth of single crystal InAs - WZ nanowire crosses</i>
P1.3	Bruno Daudin Université Grenoble Alpes and CEA-Grenoble, INAC PHELIQS/NPSC, France <i>Assessment of p-n junction in GaN single NWs by nanocathodoluminescence and electron beam induced current</i>
P1.4	Luca Gagliano Eindhoven University of Technology, The Netherlands <i>Pseudo-direct to direct compositional crossover in wurtzite GaP/In_xGa_{1-x}P core-shell nanowires</i>
P1.5	Alexander Dobrovolsky Chemical Physics and Nano Lund, Lund University, Sweden <i>Photoluminescence microscopy of single metal-halide perovskite nanowires: effect of crystal phase transition</i>
P1.6	Daria Beznasiuk Université Grenoble-Alpes and CNRS-Institut Néel, Grenoble, France <i>Dislocations free axial InAs-on-GaAs nanowires below critical diameter on Si substrates</i>
P1.7	Hanno Küpers Paul-Drude-Institut für Festkörperelektronik, Berlin, Germany <i>Consequences of the deposition sequence inherent to the growth of nanowire shells in molecular beam epitaxy</i>
P1.8	Oscar W. Kennedy London Centre for Nanotechnology, University College London, United Kingdom <i>MBE growth of ZnO nanowires with perpendicular polar and growth axes</i>
P1.9	Ning Han Institute of Process Engineering, Chinese Academy of Sciences, Beijing, China <i>Orientation dependent photovoltaics of GaAs nanowires</i>
P1.10	Lert Chayanun Synchrotron radiation research, Lund University, Sweden <i>X-ray beam induced current (XBIC) imaging of a single n-i-n doped InGaP nanowire device</i>
P1.11	Jung-Hyun Kang Braun Center for Submicron Research, Weizmann Institute of Science, Rehovot, Israel <i>Reclining InAs nanowires and intersections in-situ side coated with Al</i>
P1.12	Satoshi Yoshimura Department of Engineering and Applied Sciences, Sophia University, Tokyo, Japan <i>Regrown InP/GaInAs core-shell nanowires by self-catalytic VLS mode</i>
P1.13	
P1.14	Miriam Boehmler neaspec GmbH, Applications Department, Martinsried, Germany <i>Nano-analytics: near-field microscopy and spectroscopy with 10 nm spatial resolution</i>
P1.15	Julian Jakob Laboratory for Applications of Synchrotron Radiation, Karlsruhe Institute of Technology, Germany <i>Simultaneous time-resolved in-situ XRD and RHEED study during the growth of GaAs nanowires</i>
P1.16	Vladislav Khayrudinov Department of Micro- and Nanosciences, Micronova, Aalto University, Finland <i>Characterization of GaAs nanowire radial p-n junctions fabricated by lithography-free isolation method</i>
P1.17	Silvia Rubini CNR-IOM, Trieste 34149, Italy <i>Full optical characterization of doping efficiency in MBE grown Te-doped</i>

P1.18	Gaute Otnes Solid State Physics and NanoLund, Lund University, Sweden <i>Doping of $\text{In}_x\text{Ga}_{1-x}\text{P}$ nanowires by diethylzinc</i>
P1.19	Lisa Liborius Institute for Semiconductor Technology / University of Duisburg-Essen, Germany <i>p-GaAs/n-InGaP heterojunction in Au-assisted MOVPE grown multi shell nanowires</i>
P1.20	Danial Bahrami Solid State Physics Department, University of Siegen, Germany <i>Electrical measurements of single as-grown semiconductor core-shell nanowires</i>
P1.21	PengYi Tang Catalan Institute of Nanoscience and Nanotechnology (ICN2), CSIC and The Barcelona Institute of Science and Technology (BIST) and Catalonia Institute for Energy Research (IREC), Spain <i>Bottom-up engineering of nanoflake and nanowire heterostructures for energy storage and conversion applications</i>
P1.22	Andrew C. Meng Department of Materials Science and Engineering, Stanford University, USA <i>Room temperature direct- and indirect-gap photoluminescence from self-passivated core-shell germanium/germanium-tin nanowires</i>
P1.23	Vladimir G. Dubrovskii St. Petersburg Academic University, Russia <i>New insights into the vapor-liquid-solid growth of III-V nanowires: incubation stage, contact angle, truncated facets and crystal structure</i>
P1.24	Andreana Daniil and Simon Escobar Steinvall Laboratory of Semiconductor Materials, École Polytechnique Fédérale de Lausanne, Switzerland <i>Characterisation of earth abundant semiconductor nanostructures based on zinc phosphide and zinc arsenide</i>
P1.25	Martin Friedl Laboratory of Semiconductor Materials, École Polytechnique Fédérale de Lausanne, Switzerland <i>Laterally-oriented InAs nanowires on GaAs substrates</i>
P1.26	Elena Alexandra Serban Department of Physics, Chemistry, and Biology (IFM), Linköping University, Sweden <i>Selective-area growth of GaN nanorods by magnetron sputter epitaxy</i>
P1.27	Xin Guan Lyon University, Lyon Institute of Nanotechnology- UMR 5270 – CNRS, France <i>GaAs nanowires for solar water splitting</i>
P1.28	Sara Martí-Sánchez Catalan Institute of Nanoscience and Nanotechnology (ICN2), CSIC and The Barcelona Institute of Science and Technology (BIST), Spain <i>Strain relaxation mechanisms in ZnSe@ZnTe core-shell nanowires grown horizontally from a guided growth approach</i>
P1.29	Eero Koivusalo Optoelectronics Research Centre, Tampere University of Technology, Finland <i>Highly uniform self-catalyzed GaAs nanowires fabricated by a lithography-free method</i>
P1.30	Jochen Bissinger Walter Schottky Institut / Technical University of Munich, Garching, Germany <i>Simulation of monolithically integrated Ga(Al)As-InGaAs core-multishell nanowire lasers on silicon waveguides</i>
P1.31	Zakaria Azad Department of Physics, University of Basel, Switzerland <i>Strain and composition effects on Raman vibrational modes of hexagonal GaP/SiGe core-shell nanowires</i>
P1.32	Olof Hutlin Solid State Physics and NanoLund, Lund University, Sweden <i>Aerotaxy GaAs nanowire pn-junctions</i>
P1.33	Bianchi Méndez Departamento Física de Materiales, Universidad Complutense de Madrid, Spain <i>Synthesis of oxide nano-heterostructures with dissimilar dimensionality by vapor solid deposition</i>
P1.34	Saskia Weiszer Walter Schottky Institut and Physics Department, Technical University Munich, Garching, Germany <i>Molecular beam epitaxy and characterization of (In,Ga)N nanowires on Si (111)</i>

P1.35	Jan Hajer Physikalisches Institut, EP3, Am Hubland, Würzburg, Germany <i>Proximity induced superconductivity in CdTe-HgTe core-shell nanowires</i>
P1.36	Bruno C. Silva Universidade Estadual de Campinas, Instituto de Física "Gleb Wataghin", Campinas, Brazil <i>Asymmetrically-shaped morphologies in wurtzite GaP nanowires</i>
P1.37	Armand Davtyan Faculty of Science and Engineering, University of Siegen, Germany <i>Characterization of types and distances of stacking faults in a wurtzite GaAs nanowire via coherent X-ray diffraction</i>
P1.38	Lena Jung I. Institute of Physics (IA), RWTH Aachen University, Germany <i>Optical resonances in silicon nanowires with doped segments investigated with infrared near-field microscopy</i>
P1.39	Sudhakar Sivakumar Solid State Physics and NanoLund, Lund University, Sweden <i>Quantitative Optical and Morphological studies on GaAsP Nanowires Grown by Aerotaxy</i>
P1.40	Elham Fadaly Kavli Institute of Nanoscience, Delft University of Technology, The Netherlands <i>Conductance quantization in InSb nanowire networks</i>
P1.41	Sara Thorberg Solid State Physics and NanoLund, Lund University, Sweden <i>Growth of mechanically stable nanowires from sub-10 nm seed particles suitable for applications in catalysis</i>
P1.42	Thomas Cossuet Université Grenoble Alpes, CNRS, France <i>ZnO / CuCrO₂ core shell nanowire heterostructures for self-powered UV photodetectors</i>
P1.43	Hung-Ling Chen Centre for Nanoscience and Nanotechnology, CNRS, University Paris-Sud/Paris-Saclay, France <i>Determination of n-type doping level in single GaAs nanowires by cathodoluminescence</i>
P1.44	Leila Balaghi Institute of Ion Beam Physics and Materials Research, Helmholtz-Zentrum Dresden-Rossendorf, Germany <i>Extremely lattice mismatched GaAs/In_xGa_{1-x}As core/shell nanowires: coherent growth and strain distribution</i>
P1.45	Hanna Kindlund Solid State Physics and NanoLund, Lund University, Sweden <i>Heteroepitaxial radial growth of zinc-blende and wurtzite structured AlSb shells on InAs nanowires</i>
P1.46	Martina Morassi Center of Nanoscience and Nanotechnology (C2N), Univ. Paris Sud and Paris-Saclay, France <i>Molecular Beam epitaxy growth and optical characterization of In-rich In_xGa_{1-x}N/GaN nanowire heterostructures</i>
P1.47	Maria Messing Solid State Physics and NanoLund, Lund University, Sweden <i>Development of a risk management organization and risk communication strategy for NanoLund</i>
P1.48	Axel R. Persson nCHREM/Centre for Analysis and Synthesis, Lund University, Sweden <i>3D reconstruction of budded nanowires</i>
P1.49	Fionán Davitt Department of Chemistry, University College Cork, Ireland <i>Chemical vapour deposition of SnSe₂ nanowires from a single source diselenoether precursor</i>
P1.50	Dingding Ren Department of Electronic Systems and Department of Physics, Norwegian University of Science and Technology (NTNU), Trondheim, Norway <i>High Q-factor, single-mode, room-temperature lasing from GaAsSb/GaAs nanowire superlattices</i>
P1.51	Yury Berdnikov St. Petersburg Academic University and ITMO University, St. Petersburg, Russia <i>Broadening of Length distributions of InAs nanowires</i>

P1.52	Andreas Liudi Mulyo Department of Electronic Systems, Norwegian University of Science and Technology (NTNU), Norway and Department of Engineering and Applied Sciences, Sophia University, Tokyo, Japan <i>Epitaxy feasibility of n-type GaN/AlGaIn nanocolumns on silica glass</i>
P1.53	Jonathan Becker and Megan Hill Walter Schottky Institut and Physik Department, Technical University of Munich, Garching, Germany <i>Comprehensive insights into Si-doping of catalyst-free InAs nanowires</i>
P1.54	Letian Dai GeePs, CNRS, CentraleSupélec, Univ Paris-Sud, France <i>Optimizing tin dioxide nanoparticles distribution for silicon nanowires growth</i>
P1.55	Tina Tauchnitz Institute of Ion Beam Physics and Materials Research, Helmholtz-Zentrum Dresden-Rossendorf, and Center for Advancing Electronics Dresden, Technische Universität Dresden, Germany <i>Decoupling the two roles of liquid Ga droplets in the self-catalyzed growth of GaAs nanowires on SiO₂/Si(111) substrates</i>
P1.56	Sabrina Sterzl Department of Physics, University of Oxford, United Kingdom <i>Catalyst-free growth of quasi-pure-phase InAsSb nanowires with enhanced carrier mobility due to Sb incorporation</i>
P1.57	Ching-Lien Hsiao Thin Film Physics Division, Department of Physics, Chemistry and Biology (IFM), Linköping University, Sweden <i>Single-crystal GaN nanorods grown on conducting templates by magnetron sputter epitaxy</i>
P1.58	David J. Hill Department of Chemistry, University of North Carolina at Chapel Hill, United States <i>Boron modulation doping and morphology control in silicon nanowire p-i-n photodiodes</i>
P1.59	Luna Namazi Solid State Physics and NanoLund, Lund University, Sweden <i>Radial wurtzite GaSb on InAs core template nanowires</i>
P1.60	Riccardo Rurali Institut de Ciència de Materials de Barcelona (ICMAB-CSIC), Spain <i>Is hexagonal Si the next big thing in nanowires?</i>

Tuesday, May 30, 2017

14:00 – 16:00 Poster Session P2

P2.1	Werner Prost Solid-State Electronics Department (HLT), Faculty of Electrical and Electronic Engineering and CENIDE, University of Duisburg-Essen, Germany <i>VLS growth of GaAs nanowires on GaN microrods by MOVPE</i>
P2.2	Fabrice Oehler Centre de Nanosciences et de Nanotechnologies, CNRS, Univ. Paris-Sud, France <i>Dynamics of the self-catalyzed growth by MBE of GaP nanowire arrays on patterned silicon - Experiments and theory</i>
P2.3	Davide Tedeschi Dipartimento di Fisica, Sapienza Università di Roma, Italy <i>Optical studies of a single crystal-phase homostructured InP nanowire</i>
P2.4	Alain Dijkstra Department of Applied Physics, Eindhoven University of Technology, The Netherlands <i>Probing the direct band gap emission in Ge/Ge_{0.87}Sn_{0.13} core/shell nanowire arrays</i>
P2.5	Aleksander B. Mosberg Department of Physics, Norwegian University of Science and Technology (NTNU), Norway <i>Exploring focused ion beam substrate patterning for nanowire growth</i>
P2.6	Diana L. Huffaker Electrical Engineering Dept., University of California, Los Angeles, United States and School of Physics and Astronomy, Cardiff University, United Kingdom <i>Advanced nanowire photodetectors at infrared wavelengths</i>
P2.7	Vladimir Kaganer Paul-Drude-Institut für Festkörperelektronik, Berlin, Germany <i>Elastic versus plastic strain relaxation in coalesced GaN nanowires</i>
P2.8	Andrea Scaccabarozzi Institut Photovoltaïque d'Île-de-France (IPVF), France <i>Substrate doping effects on the MBE growth of self-catalyzed GaP, GaAs and GaAsP nanowires on patterned Si substrates</i>
P2.9	Xin Yan State Key Laboratory of Information Photonics and Optical Communications, Beijing University, China <i>A room-temperature nanowire/quantum-well near-infrared laser</i>
P2.10	Martin Hetzl Walter Schottky Institut and Physics Department, Technische Universität München, Garching, Germany <i>Band gap engineering by strain in selectively grown GaN-(Al,Ga)N core-shell nanowire heterostructures</i>
P2.11	Mitchell Robson Dept. of Engineering Physics, Centre for Emerging Device Technologies, McMaster University, Canada <i>Multispectral absorption in large-diameter InAsSb nanowire arrays for infrared photodetection</i>
P2.12	Kohei Takano Dept. of Engineering and Applied Sciences, Sophia University, Tokyo, Japan <i>Photoluminescence characteristics of InP/GaInAs heterostructure nanowires grown by self-catalytic VLS mode</i>
P2.13	Marcus Tornberg Solid State Physics and NanoLund, Lund University, Sweden <i>Towards directional control of MOVPE-grown InAs nanowires</i>
P2.14	Bang Li State Key Laboratory of Information Photonics and Optical Communications, Beijing University of Posts and Telecommunications, China <i>A nanowire phototransistor with negative photoresponse</i>
P2.15	Philipp Schroth Department of Physics, University of Siegen, and Laboratory for Application of (LAS) and Institute for Photon Science and Synchr. Radiation (IPS), Karlsruhe Institute of Technology, Germany <i>Investigation of the interplay between droplet shape and polytypism in GaAs nanowires</i>
P2.16	Jesús Herranz Paul-Drude-Institut für Festkörperelektronik, Berlin, Germany <i>Coaxial (In,Ga)As/GaAs dot-in-a-well structures for 1.3 μm light emission from nanowires grown on Si</i>

P2.17	Ali Al Hassan Naturwissenschaftlich- Technische Fakultät der Universität Siegen, Germany <i>In-plane X-ray diffraction on single GaAs/(In,Ga)As/GaAs core-shell nanowires</i>
P2.18	Michael S. Seifner Institute of Materials Chemistry, TU Wien, Vienna, Austria <i>Low temperature nucleation and growth of Ge_{1-x}Sn_x nanowires</i>
P2.19	Mahdi Zamani Laboratory of Semiconductor Materials, École Polytechnique Fédérale de Lausanne, Switzerland <i>Growth and correlation between optical and structural properties of GaAs(111)A nanowires</i>
P2.20	Wei Zhang Division of Chemical Physics and NanoLund, Lund University, Sweden <i>Carrier recombination processes in gallium indium phosphide nanowires</i>
P2.21	Parsian K. Mohseni Microsystems Engineering and NanoPower Research Laboratories, Rochester Institute of Technology, United States <i>Selective-area van der Waals epitaxy of InAsP nanowires on two-dimensional nanosheets: III-V integration on graphene, h-BN, and MoS₂</i>
P2.22	Irene Geijselaers Solid State Physics and NanoLund, Lund, Sweden <i>Optical studies on wurtzite-zinc-blende interfaces in GaAs nanowires</i>
P2.23	Naoki Fukata International Center for Materials Nanoarchitectonics, National Institute for Materials Science, Tsukuba, Japan <i>Control of hole gas accumulation of core-shell nanowires using Si and Ge radial heterostructures</i>
P2.24	Seokhyoung Kim Department of Chemistry, University of North Carolina at Chapel Hill, United States <i>Optical resonances in subwavelength single-nanowire gratings</i>
P2.25	Alexandr A. Koriakin St. Petersburg Academic University, Russia <i>Influence of elastic stresses on growth mechanism of Au-catalyzed GaAs nanowires</i>
P2.26	Lucas Güniat Laboratory of Semiconductor Materials, École Polytechnique Fédérale de Lausanne, Switzerland <i>In situ monitoring of Ge nanowire growth process in a CVD reactor</i>
P2.27	Gabriele Calabrese Paul-Drude-Institut für Festkörperelektronik, Berlin, Germany <i>Suppression of interfacial reactions during the growth of uncoalesced GaN nanowires on Ti layers sputtered on Al₂O₃(0001)</i>
P2.28	Wonjong Kim Laboratory of Semiconductor Materials, École Polytechnique Fédérale de Lausanne, Switzerland <i>Post-annealing studies on GaAs nanowires towards quantum devices</i>
P2.29	Zbigniew R. Zytewicz Institute of Physics, Polish Academy of Sciences, Warsaw, Poland <i>Kinetics of self-induced formation of GaN nanowires on amorphous substrates by PAMBE: RHEED measurements and insight into the nucleation mechanism</i>
P2.30	Anders Gustafsson Solid State Physics and NanoLund, Lund, Sweden <i>Low-temperature cathodoluminescence investigations of III-V and III-nitride nanowires</i>
P2.31	Valerio Piazza C2N, UMR9001 CNRS, University Paris Sud, University Paris Saclay, France <i>Electron beam induced current investigation of GaN Nanowires containing AlN/GaN Multiple Quantum Discs</i>
P2.32	Miroslav Kolibal Institute of Physical Engineering and CEITEC – Central European Institute of Technology, Brno University of Technology, Czech Republic <i>Bimetallic catalysts: unintentional formation by reaction with the substrate and rational design</i>
P2.33	Robert Hallberg Solid State Physics and NanoLund, Lund, Sweden <i>InAs nanowires seeded from high melting point metal nanoparticles</i>

P2.34	Mathieu Dechaux UCA, CRHEA-CNRS, Valbonne and Clermont Université, Institut Pascal, Clermont-Ferrand, and CNRS, UMR 6602, Institut Pascal, Aubière, France <i>Lasing effect under optical pumping in single p-i-n core-shell GaN nanowires grown by metalorganic chemical vapor deposition</i>
P2.35	Seyed Mohammad Mostafavi Kashani Department of Physics, University of Siegen, Germany <i>Dynamics of annealing of GaAs nanostructures (nanowires and crystallites) by in-situ time-resolved X-ray diffraction</i>
P2.36	Hermann Detz Centre for Micro- and Nanostructures, Institute for Solid State Electronics, TU Wien, and Austrian Academy of Sciences, Austria <i>Growth of self-catalyzed GaAs nanowires via focused ion beam implantation</i>
P2.37	Thomas Stettner Walter Schottky Institut and Physics Department, Technische Universität München, Garching, Germany <i>GaAs-AlGaAs core-shell nanowire lasers on silicon</i>
P2.38	Zhaoguo Xue National Laboratory of Solid State Microstructures, Nanjing University, China and LPICM, CNRS, Ecole Polytechnique, Université Paris-Saclay, France <i>Engineering island-chain silicon nanowires via a droplet mediated Plateau-Rayleigh transformation</i>
P2.39	Erik K. Mårtensson Solid State Physics and NanoLund, Lund, Sweden <i>Side-by-side MOVPE study of GaAs nanowire growth using gold, silver and gold-silver alloys as seed materials</i>
P2.40	Diana Car Department of Applied Physics, Eindhoven University of Technology and Kavli Institute of Nanoscience, Delft University of Technology, The Netherlands <i>InSb nanowires with built-in Ga_xIn_{1-x}Sb tunnel barriers for Majorana devices</i>
P2.41	Simone Assali Department of Engineering Physics, École Polytechnique de Montréal, Canada <i>Structural and optical properties of SiGeSn nanowires</i>
P2.42	Thomas Cossuet Université Grenoble Alpes, CNRS, France <i>Polarity-dependent selective area growth of ZnO nanowires by chemical bath deposition</i>
P2.43	Tomáš Pejchal CEITEC – Central European Institute of Technology, Brno University of Technology, Czech Republic <i>Group III catalysts: preparation and Ge nanowire growth</i>
P2.44	Suneel Kodambaka Solid State Physics and NanoLund, Lund, Sweden and Department of Materials Science and Engineering, University of California Los Angeles, United States <i>Kinetics of Au-catalyzed evaporation of GaAs nanowires</i>
P2.45	Daniel Ruhstorfer Walter Schottky Institut and Physics Department, Technische Universität München, Garching, Germany <i>Size-, defect- and disorder-mediated quantum confinement phenomena in GaAs-based nanowires</i>
P2.46	Mahtab Aghaeipour Solid State Physics and NanoLund, Lund, Sweden <i>Enhanced light-trapping in InP nanowires</i>
P2.47	Xulu Zeng Solid State Physics and NanoLund, Lund, Sweden <i>GaInP/InP nanowire tunnel diodes for tandem solar cells</i>
P2.48	Chalermchai Himwas Centre de Nanosciences et de Nanotechnologies, CNRS, Univ. Paris-Sud, France <i>Catalyst-free GaAsP/GaP core/shell nanowires for tandem solar application</i>
P2.49	Genziana Bussone Beamline P08, PETRA III synchrotron, DESY, Hamburg, Germany <i>Synchrotron X-ray diffraction on ensemble and individual core/shell GaAs/In_xGa_{1-x}As nanowires at beamline P08 – PETRA III (DESY)</i>
P2.50	Marie-Ingrid Richard Aix-Marseille Université, CNRS and ESRF, The European Synchrotron, Grenoble, France <i>Intermixing in single Ge-Si core-shell nanowires: a coherent X-ray imaging study</i>

P2.51	David J.O. Göransson Solid State Physics and NanoLund, Lund, Sweden <i>Aharonov-Bohm effect in selective area grown InP-InAs core-shell nanowires</i>
P2.52	Nikolai V. Sibirev St. Petersburg Academic University and St. Petersburg State University, Russia <i>Zinc blende GaN nanowires formation</i>
P2.53	Carina B. Maliakkal Department of Condensed Matter Physics and Materials Science, Tata Institute of Fundamental Research, Mumbai, India <i>Characterization of wurtzite GaP-based core-shell nanowires</i>
P2.54	Joël Eymery University Grenoble Alpes, Nanostructures and Synchrotron Radiation Laboratory, CEA, Grenoble, France <i>Flexible capacitive piezoelectric sensor based on vertical GaN wires</i>
P2.55	Roy L.M. Op het Veld QuTech, Delft University of Technology and Department of Applied Physics, Eindhoven University of Technology, The Netherlands <i>Shadowed superconducting islands on InSb nanowire networks</i>
P2.56	Sofie Yngman Synchrotron Radiation Research, Lund University, Sweden <i>GaN nanowires as probes for scanning probe microscopy</i>
P2.57	Vilgailė Dagytė Solid State Physics and NanoLund, Lund, Sweden <i>Aspects of time-resolved photoluminescence characterization of dense as-grown GaAs nanowire arrays with photovoltaic perspective</i>
P2.58	
P2.59	Pavel Geydt Laboratory of Solid State Physics, Lappeenranta University of Technology (LUT), Finland <i>Elastic modulus of wurtzite InP nanowires and method for accurate measurements of tapered nanowires by advanced quantitative AFM</i>
P2.60	Egor D. Leshchenko ITMO University and St. Petersburg Academic University, St. Petersburg, Russia <i>Inhomogeneous Be doping in GaAs nanowires</i>

Thursday, June 1, 2017

14:00 – 16:00 Poster Session P3

P3.1	Adam M. Burke Solid State Physics and NanoLund, Lund University, Sweden <i>Electrostatically side-gated double quantum dots in InAs nanowires</i>
P3.2	Imad Ibrahim Center for Advancing Electronics Dresden (cfaed), TU Dresden, Germany <i>Realization of in-situ arsenic-doping of CVD grown silicon nanowires</i>
P3.3	Xiaojun Su Division of Chemical Physics and NanoLund, Lund, Sweden <i>Effect of HCl etching on carrier recombination processes in InP semiconductor nanowires</i>
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P3.6	Andrew C. Meng Department of Materials Science and Engineering, Stanford University, United States <i>Quantitative analysis of interface states in bulk and nanostructured semiconductors using electrochemical impedance spectroscopy</i>
P3.7	Anjan Mukherjee Department of Electronic Systems, Norwegian University of Science and Technology (NTNU), Norway <i>Embedded single GaAs nanowire/graphene hybrid devices fabricated by a position controlled micro transfer and imprinting technique</i>
P3.8	Anna Sitek School of Science and Engineering, Reykjavik University, Iceland and Department of Theoretical Physics, Wrocław University of Science and Technology, Poland <i>Excitons in core-shell quantum rings</i>
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P3.34	Martin Josefsson Solid State Physics and NanoLund, Lund University, Sweden <i>High thermoelectric efficiency of an InAs/InP nanowire quantum dot</i>

P3.35	Masiar Sistani Institute for Solid State Electronics, Technische Universität Wien, Vienna, Austria <i>Room temperature quantum ballistic transport in monolithic ultrascaled Al-Ge-Al nanowire heterostructures</i>
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P3.59	Pablo Romero-Gomez Laboratory of Semiconductor Materials, École Polytechnique Fédérale de Lausanne, Switzerland <i>Robust nanowire arrays for new generation solar cells</i>
P3.60	Patrick Zellkens Peter Grünberg Institut 9, Forschungszentrum Jülich, Germany and JARA-FIT, Fundamentals of Future Information Technology <i>Electron interference and spin-orbit coupling in GaAs/InSb core/shell nanowires</i>



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